

CLAIMS

~~1. A thin gold-alloy wire for a semiconductor device having excellent corrosion resistance, in a thin gold-alloy wire for a semiconductor device which is resin-molded at a high temperature, which comprises 50 to 3000 ppm by weight of Mn with the balance comprising gold and unavoidable impurities.~~

2. A thin gold-alloy wire for a semiconductor device according to claim 1, wherein the content of Mn is 50 to 100 ppm by weight.

3. A thin gold-alloy wire for a semiconductor device according to claim 1, wherein further the content of at least one member selected from the group consisting of Be and B is 1 to 20 ppm by weight in total.

4. A thin gold-alloy wire for a semiconductor device according to claim 1, wherein further the content of at least one member selected from the group consisting of Ca, Sr and rare earth elements is 1 to 30 ppm by weight in total.

5. A thin gold-alloy wire for a semiconductor device according to claim 3, wherein further the content of at least one member selected from the group consisting of Ca, Sr and rare earth elements is contained within a range of 1 to 30 ppm by weight in total.

6. A thin gold-alloy wire for a semiconductor device according to claim 4, wherein further the content of at least one member selected from the group consisting of In and Tl is 1 to 50 ppm by weight in total.

~~7. A thin gold-alloy wire for a semiconductor device according to claim 5, wherein further the content of at least one member selected from the group consisting of In and Tl is 1 to 50 ppm by weight in total.~~

Replaced by new claim 1



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